

Model RFP-100200N4X50-2

RF Power

Aluminum Nitride Terminations 30 Watts, 50 Ω



Features

- DC 3.0 GHz
- 30 Watts
- Aluminum Nitride (AIN) Ceramic
- Terminal for Lead Attachment
- Non-Nichrome Resistive Element
- Low VSWR
- 100% Tested

General Specifications

Resistive Element: Thick film

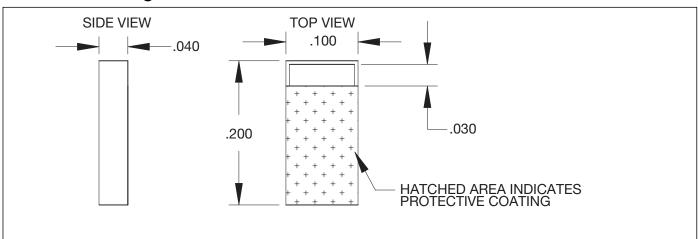
Substrate: Aluminum nitride ceramic Terminals: Tin/Lead, 90/10 over nickel

Electrical Specifications

Resistance Value:50 ohms, ±2%Frequency Range:DC - 3.0 GHzPower:30 WattsV.S.W.R.:1.25:1

Notes: Tolerance is $\pm .010$, unless otherwise specified. Operating temperature is -55° C to $+150^{\circ}$ C (see chart). Designed to meet or exceed applicable portions of MIL-E-5400. All dimensions are in inches. **Specifications subject to change without notice.**

Outline Drawing



VER. 12/5/01

Available on Tape and Reel for Pick and Place Manufacturing.

Sales Desk USA: Voice: (800) 544-2414 Fax: (315) 432-9121 Sales Desk Europe: Voice: (+44) 23 92 232392 Fax: (+44) 23 92 251369

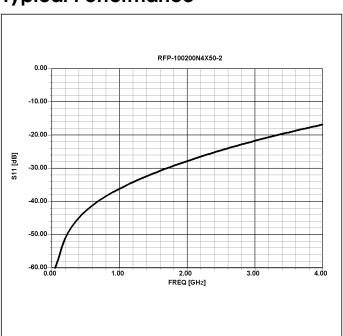


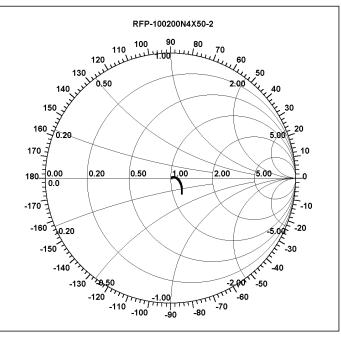
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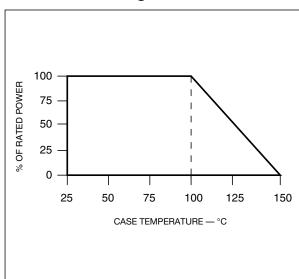


Typical Performance

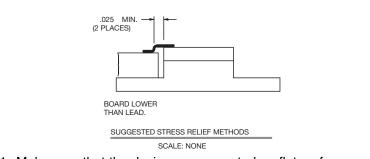




Power Derating



Suggested Mounting Procedures



- 1. Make sure that the devices are mounted on flat surfaces (.001" under the device) to optimize the heat transfer.
- 2. Position device on mounting surface and solder in place using an SN96 type solder.
- 3. Solder leads in place using an SN63 type solder with a controlled temperature iron (700°F).

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